

FDC3535

P-Channel Power Trench[®] MOSFET, -80 V, -2.1 A, 183 mΩ

Product Overview

For complete documentation, see the data sheet.

This P-Channel MOSFET is produced using an advanced Power Trench[®] process that has been optimized for rDS(on), switching performance and ruggedness.

Features

- Max rDS(on) = 183 mΩ at VGS = -10 V, ID = -2.1 A
- Max rDS(on) = 233 mΩ at VGS = -4.5 V, ID = -1.9 A
- High performance trench technology for extremely low rDS(on)
- High power and current handling capability in a widely used surface mount package
- Fast switching speed
- 100% UIL Tested
- RoHS Compliant

Applications

- This product is general usage and suitable for many different applications.

| Product | Pricing (\$/Unit) | Compliance | Status | Channel Polarity | Configuration | V _{DS(BR)Min} (V) | V _{GSMax} (V) | V _{GS(t)hMax} (V) | IDMax (A) | PDMax (W) | R _{DS(on)Max} @ VGS = 2.5 V (mΩ) | R _{DS(on)Max} @ VGS = 4.5 V (mΩ) | R _{DS(on)Max} @ VGS = 10 V (mΩ) | Q _g Typ @ VGS = 4.5 V (nC) | Q _g Typ @ VGS = 10 V (nC) | C _{iss} Typ (pF) | Package Type |
|---------|-------------------|------------|--------|------------------|---------------|----------------------------|------------------------|----------------------------|-----------|-----------|---|---|--|---------------------------------------|--------------------------------------|---------------------------|--------------|
| FDC3535 | 0.2488 | | Active | P-Channel | Single | -80 | ±20 | -3 | -2.1 | 1.6 | - | 233 | 183 | - | 6.8 | 659 | TSOT-23-6 |